



ZHEJIANG UNIU-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



U3502C Data Sheet

V 1.1

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100V Input, Switching Current Limit Step-Down Converter

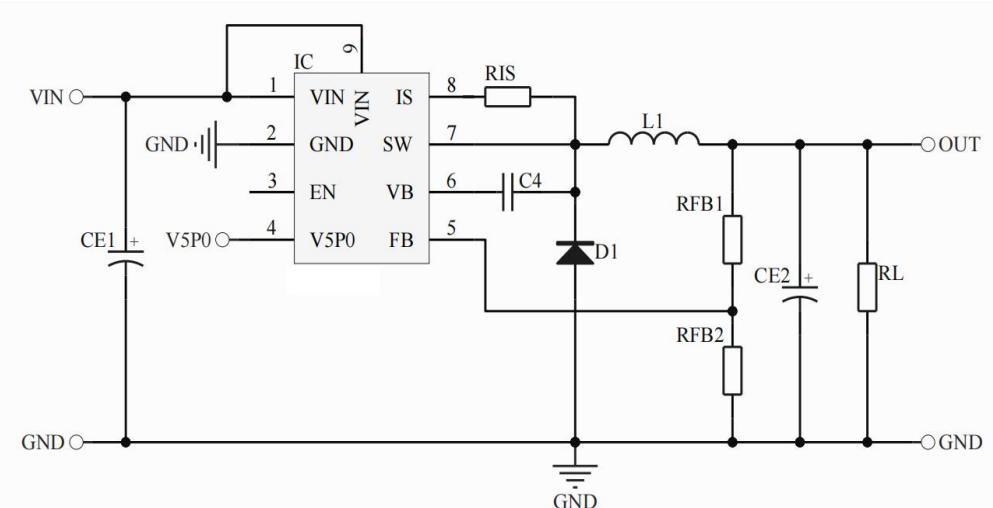
General Description

The U3502C is a high voltage, step-down, switching regulator built-in MOSFET. It integrates a high-side, high-voltage, power MOSFET with a current limit of 3A(I_{PK}) typically. The input ranges accommodates a variety of step-down applications, making it ideal for automotive, industry, and lighting applications. Hysteretic voltage-mode control is employed for very fast response. UNIU's proprietary feedback control scheme minimizes the number of required external components.

The switching frequency is 150KHz, allowing for small component size. Thermal shutdown and short-circuit protection (SCP) provide reliable and fault-tolerant operations. Low quiescent current allows the U3502C to be used in battery-powered applications.

The U3502C is available in a ESOP-8 package with an exposed pad.

Simplified Application



Key Features

- Integrated 200V high voltage start circuit
- Integrated 5.5V reference
- Built-In 100V/135 m Ω MOSFET
- Built-in Bootstrap Diode
- Hysteretic Control: No Compensation
- 150 KHz Switching Frequency
- PWM Dimming Control Input for step-down Application
- Short-Circuit Protection (SCP) with Integrated High-Side MOSFET
- Low Quiescent Current
- Thermal Shutdown
- Available in a ESOP-8 Package with an Exposed Pad

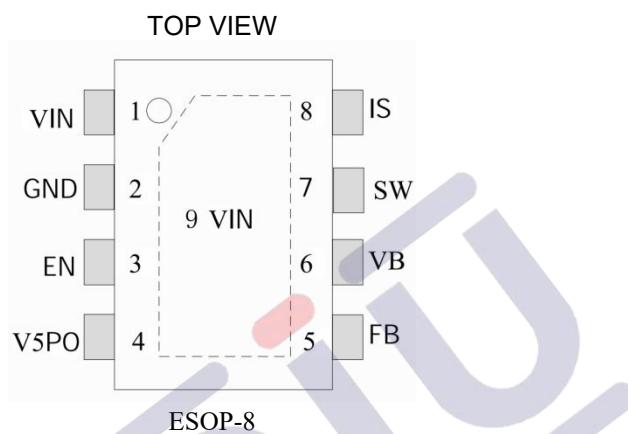
Applications

- Scooters, E-Bike Control Power Supplies
- Solar Energy Systems
- Automotive System Power
- Industrial Power Supplies
- High-Power LED Drivers
- USB

Ordering Information

Part Number	Package	Vo	VIN MAX	I _{PK}	Description
U3502C	ESOP-8	>2V	100V	3A	4000Pcs/Reel

Pin Description



Pin Functions

ESOP-8 Pin #	Name	Description
1	VIN	Input supply. VIN supplies power to all of the internal control circuitries.
2	GND	Ground.
3	EN	En input. Default suspension, built-in resistance
4	V5P0	The output voltage is 5.5V (Max current is 5mA)
5	FB	Feedback. FB is the input to the voltage hysteretic comparators.
6	VB	VB is the positive power supply for the internal, floating, high-side MOSFET driver. Connect a bypass capacitor between VB and SW.
7	SW	Switch node.
8	IS	Current detection. Current Sensing Input.
9	EP	Input supply. VIN supplies power to all of the internal control circuitries.

Block Diagram

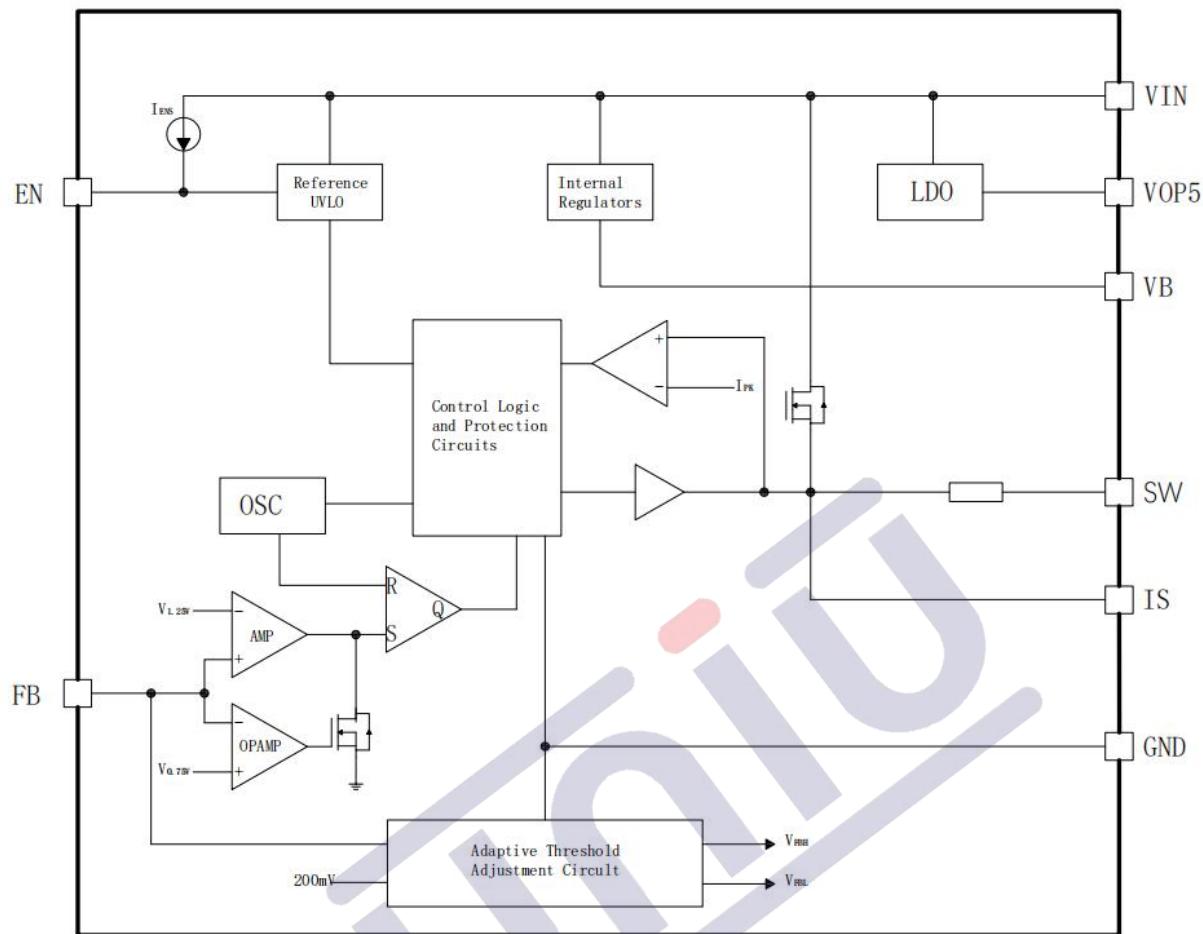


Figure 1: Function Block Diagram

Absolute Maximum Ratings (Note 1)

Parameter	Value	Unit
VIN,SW,IS Pin Voltage Range	-0.3 to 200	V
VB Supply Voltage	200+20	V
FB, EN Voltage Range	-0.3 to 7	V
Package Thermal Resistance ---Junction to Ambient (ESOP-8)	165	°C/W
Maximum Junction Temperature	160	°C
Storage Temperature Range	-65 to 150	°C
Lead Temperature (Soldering, 10sec.)	260	°C
ESD Capability, HBM (Human Body Model)	2	kV
ESD Capability, MM (Machine Model)	200	V

Note: For electrostatic sensitive devices, pay attention to ESD prevention measures when operating them.

Electrical Characteristics

$V_{IN} = 50V$, $T_A = +25^\circ C$, unless otherwise noted. Specifications over temperature are guaranteed by design and characterization.

Parameter	Symbol	Condition	Min	Typ	Max	Units
V_{5P0}	V_{V5P0}	$V_{IN}=60V$	—	5.5	—	V
Shutdown supply current		$V_{EN} = 0V$	—	4	—	μA
Quiescent supply current		No load, DIM = low, $V_{FB} = 1.4V$	—	0.7	—	mA
Upper switch on resistance	$R_{DS(ON)}$	$V_{VB} - V_{SW} = 12V$	—	110	135	$m\Omega$
Upper switch leakage current	I_{SWLK}	$V_{EN} = 0V$, $V_{SW} = 0V$	—	0.02	1.5	μA
Current limit	I_{PK}	$V_{FB} = 1.3V$	—	3	—	A
Working frequency	F_{SW}		—	150	—	KHz
EN -on	V_{ENH}		—	2.4	7	V
EN -off	V_{ENL}		—	—	1	V
EN threshold hysteresis	V_{ENHY}		—	500	—	mV
Feedback voltage threshold	V_{FBH}		1.25	1.30	—	V
FB to ground resistance	R_{FB}		—	50K	—	Ω
Thermal shutdown		Trigger thermal shutdown	—	150	—	$^\circ C$
		Hysteresis	—	20	—	

NOTES:

Note1. Stresses listed as the above “Maximum Ratings” may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to maximum rating conditions for extended periods may remain possibility to affect device reliability.

Note2. The device is not guaranteed to function outside its operating conditions.

Note3. Guaranteed by design.

Operation

Hysteresis Current Control with Adaptive Threshold Adjustment

The U3502C operates in a hysteretic voltage-control mode to regulate the output voltage. FB is connected to the tap of a resistor divider, which determines the output voltage. The power MOSFET is turned on when the FB voltage (V_{FB}) rises to FBon and remains on until V_{FB} rises to FBoff. The power MOSFET is turned off when V_{FB} drops to FBoff and remains off until V_{FB} falls to FBon. The two thresholds of FBon and FBoff are adjusted adaptively to compensate for all the circuit delays, so the output voltage is regulated with an average 1.30V value at FB.

Floating Driver and Bootstrap Charging

The floating power MOSFET driver is powered by an external bootstrap capacitor.

The bootstrap capacitor is charged and regulated to about 12V by the dedicated internal bootstrap regulator.

If the internal circuit does not have sufficient voltage, and the bootstrap capacitor is not sufficiently charged, extra external circuitry can be used to ensure that the bootstrap voltage is in the normal operating region. Refer to the External Bootstrap Diode section for more details.

Fast charging Function for USB Applications

Because the FB reference of the U3502C is very flexible, it is recommended to use the U3502C for USB Fast charging Applications by connecting the current sense resistor between FB and GND.

Thermal Shutdown

Thermal shutdown is implemented to prevent the chip from operating at exceedingly high temperatures. When the silicon die temperature is higher than its upper threshold, the entire chip shuts down. When the temperature is lower than its lower threshold, the chip is enabled again.

Output Short Protection

The output voltage is well-regulated when V_{FB} is around 1.30V. If the output is pulled low in over-current protection (OCP) or is shorted to GND directly, V_{FB} is low, even though the power MOSFET is turned on. The U3502C regards the low V_{FB} as a failure. The power MOSFET shuts off if the failure time is longer than 10 μ s. The U3502C attempts operation again after a delay of about 300 μ s.

The power MOSFET current is also accurately sensed via a current sense MOSFET. If the current is over the current limit, the IC is shut down. This offers extra protection under output-short conditions.

Application Information

Setting the Output Voltage

The output voltage (V_{OUT}) is set by a resistor divider (R1 and R2) (see the Typical Application on page 1). To achieve good noise immunity and low power loss, R2 is recommended to be in the range of 1k Ω to 50k Ω . R1 can then be determined with Equation (1):

$$R1 = \frac{V_{OUT} - V_{FB}}{V_{FB}} \times R2 \quad (1)$$

Where V_{FB} is 1.30V, typically.

FB has 50K resistance inside, and the calculation is in parallel with R2

Output Capacitor and Frequency Setting

The output capacitor (C_{OUT}) is necessary for achieving a smooth output voltage. The ESR of the capacitor should be sufficiently large compared to the capacitance; otherwise, the system may behave in an unexpected way, and the current ripple may be very high. V_{FB} changes from 1.25V to 1.35V when the power MOSFET switches on. To charge the capacitor and generate 1.35V at FB, the system needs ESR and some inductor current. For example, for a 5V V_{OUT} , if the forward capacitor is 0.1 μ F, the suggested ESR range of the output capacitor is 100m Ω to 250m Ω . Tantalum or aluminum electrolytic capacitors with a small ceramic capacitor are recommended.

A forward capacitor across R1 is recommended when the output capacitor is tantalum or aluminum electrolytic, which can set the desired frequency if the output capacitor and ESR cannot be changed. The forward capacitor can reduce the output voltage ripple.

In some application, simply a forward capacitor may not get proper frequency, then we can add a forward resistor in series with the forward capacitor or even more add a ceramic on the output.

Selecting the Inductor

The inductor (L) is required to convert the switching voltage to a smooth current to the load. Although the output current is low, it is recommended that the inductor current be continuous in each switching period to prevent reaching the current limit. Calculate the inductor value with Equation (2):

$$L = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{F_{SW} \times I_{OUT} \times V_{IN} \times K} \quad (2)$$

Where K is a coefficient of about 0.15 ~ 0.85

Output Rectifier Diode

The output rectifier diode supplies current to the inductor when the high-side switch is off. To reduce losses due to the diode forward voltage and recovery times, use a Schottky diode. The average current through the diode can be approximated with Equation (3):

$$I_D = I_{OUT} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (3)$$

Choose a diode with a maximum reverse voltage rating greater than the maximum input voltage and a current rating is greater than the average diode current.

Input Capacitor (C_{IN})

The input current to the step-down converter is discontinuous and therefore requires a capacitor to supply AC current to the step-down converter while maintaining the DC input voltage. Use low ESR capacitors for the best performance, especially under high switching frequency applications.

The RMS current through the input capacitor can be calculated with Equation (4):

$$I_{IN_AC} = I_{OUT} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right)} \quad (4)$$

With low ESR capacitors, the input voltage ripple can be estimated with Equation (5):

$$\Delta V_{IN} = \frac{I_{OUT} \times V_{OUT}}{F_{SW} \times C_{IN} \times V_{IN}} \times \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad (5)$$

Choose an input capacitor with enough RMS current rating and enough capacitance for small input voltage ripples.

When electrolytic or tantalum capacitors are applied, a small, high-quality ceramic capacitor (i.e.: 0.1μF) should be placed as close to the IC as possible.

External Bootstrap Diode

An external bootstrap diode may enhance the efficiency of the converter (see Figure 2).

The bootstrap diode can be a low-cost one, Optimize circuit structure, save cost, and reduce error rate for peripheral circuit configuration.

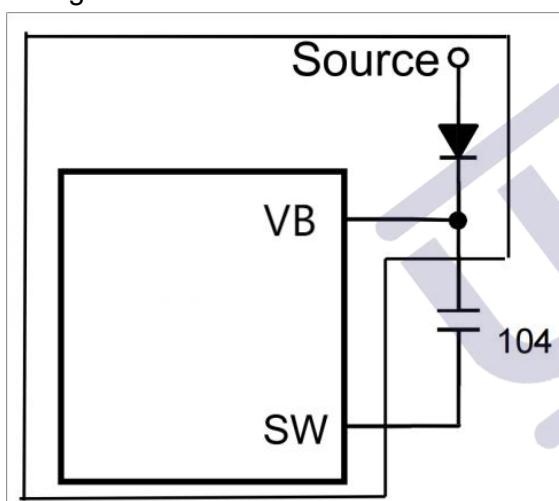


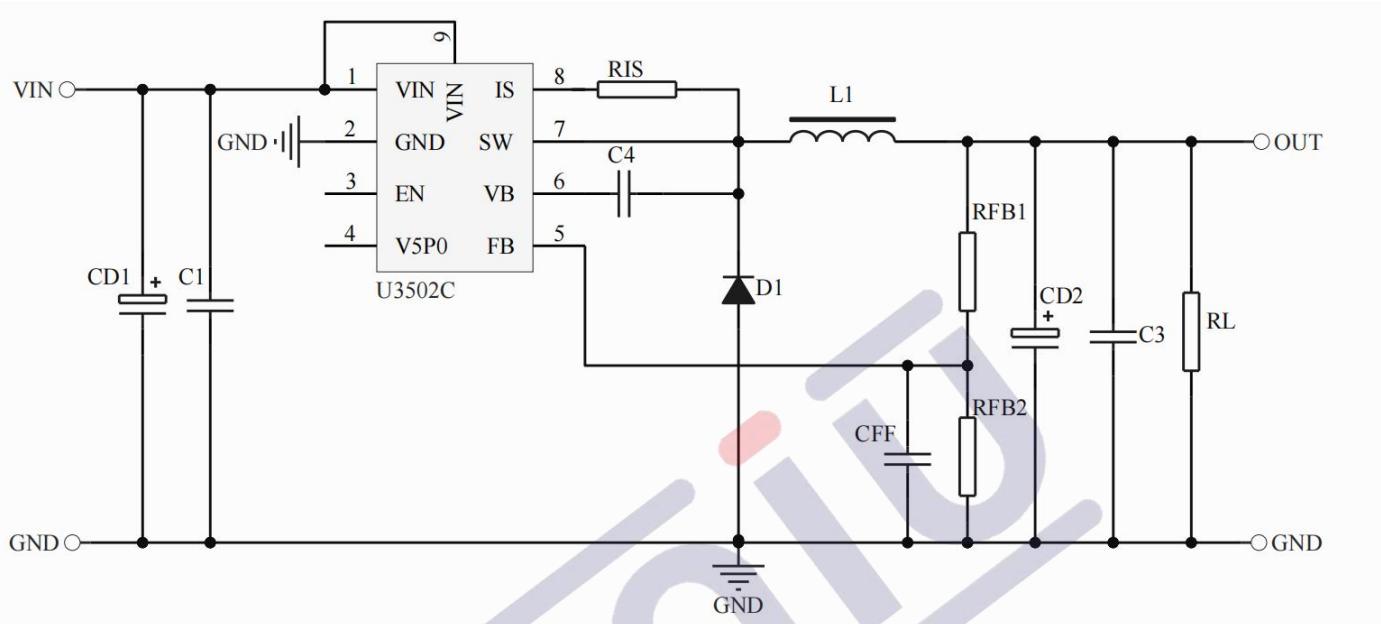
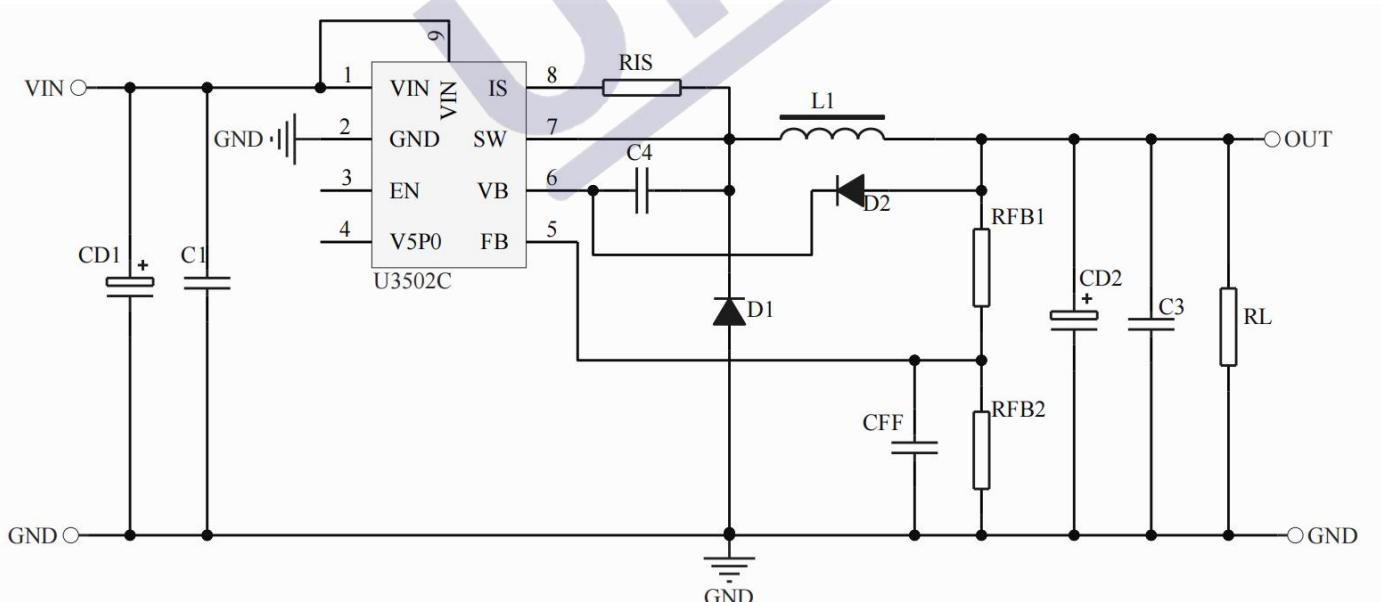
Figure 2: External Bootstrap Diode

PCB Layout Guidelines

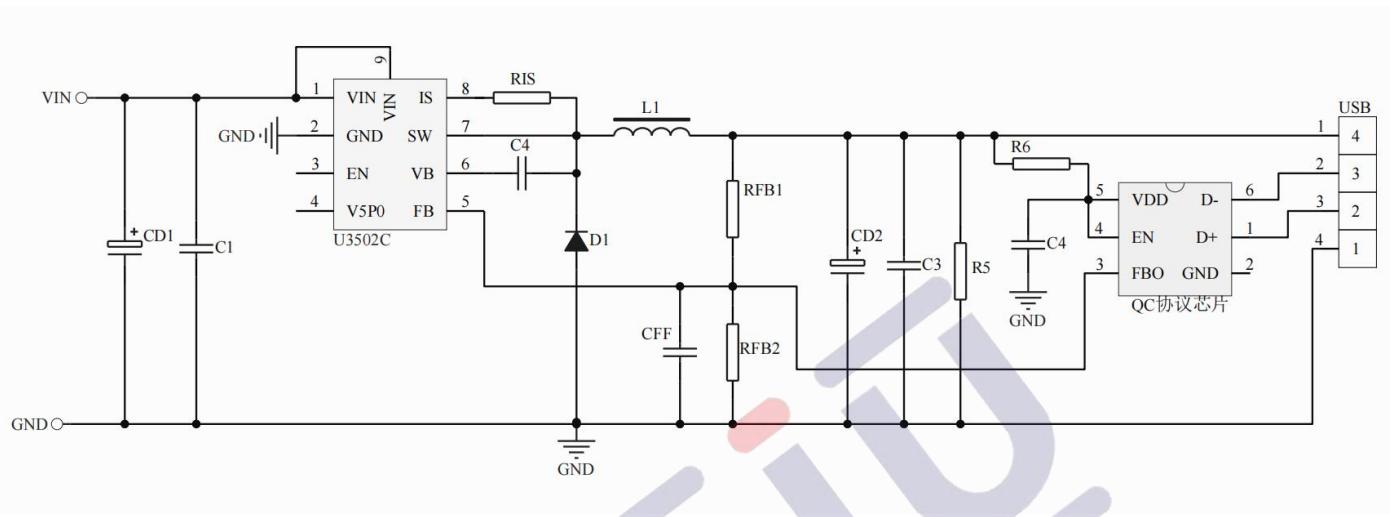
Efficient PCB layout is critical for stable operation. For best results, refer to Figure 3 and follow the guidelines below.

1. Place the input decoupling capacitor, catch diode, and the U3502C (VIN, SW, and PGND) as close to each other as possible.
2. Keep the power traces very short and fairly wide, especially for the SW node. This can help greatly reduce voltage spikes on the SW node and lower the EMI noise level.
3. Run the feedback trace as far from the inductor and noisy power traces (like the SW node) as possible.
4. Place thermal vias with 15mil barrel diameter and 40mil pitch (distance between the centers) under the exposed pad to improve thermal conduction.

Typical Application Circuit

APP1: $V_{OUT} < 10V$ APP2: $V_{OUT} = 10\sim 15V$ 

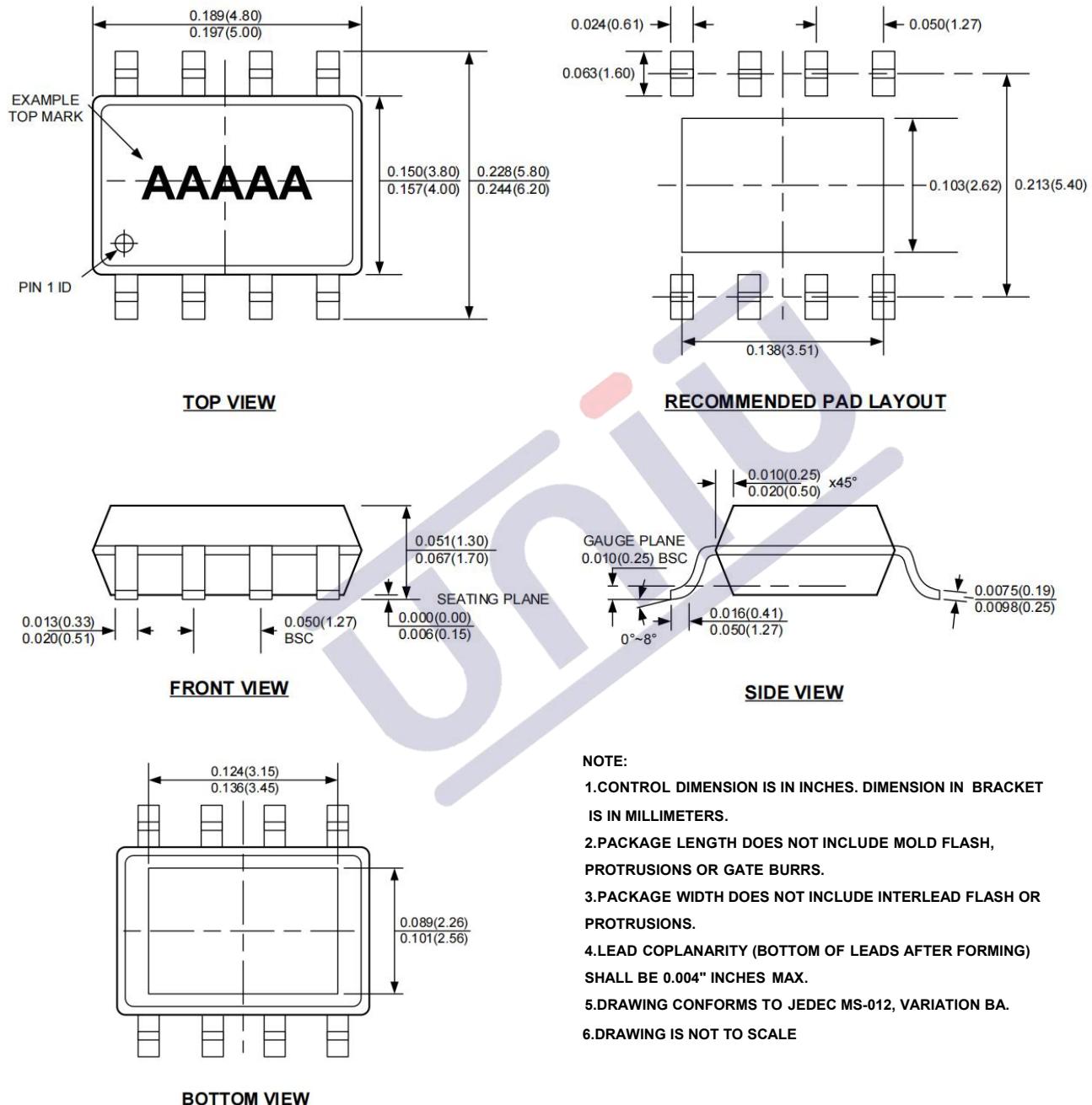
APP3: QC2.0/QC3.0



Note: Typical application circuit and parameters for reference, the actual application circuit parameters please set on the basis of measurement, mass production please communicate with the original factory, other unknown please contact our engineers.

Package Information

ESOP-8 (EXPOSED PAD)



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1、版本记录

DATE	REV.	DESCRIPTION
2023/2/25	1.0	首次发布
2023/7/12	1.1	优化参数

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